

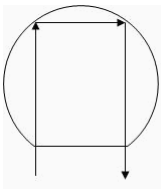
Part Number

Customer

| Category      |      | Parameter                                       | Specification                                 | Measurement Method                             |
|---------------|------|-------------------------------------------------|-----------------------------------------------|------------------------------------------------|
| OverallWafer  | 1.0  | Diameter                                        | 100.00 +/- 0.50 mm                            | WaferVendor                                    |
|               | 2.0  | Primary Flat Orientation                        | <110> +/- 1 degree                            | Wafer Vendor                                   |
|               | 3.0  | Primary Flat Length                             | 32.50 +/- 2.50 mm                             | Wafer Vendor                                   |
|               | 4.0  | Secondary Flat Orientation                      | none                                          | Wafer Vendor                                   |
|               | 5.0  | Overall Thickness                               | 1,051.00 +/- 7.00 um                          | Guaranteed by Process                          |
|               | 6.0  | Total Thickness Variation (TTV)                 | <5.00um                                       | Guaranteed by Process                          |
|               | 7.0  | Bow                                             | <40.00um                                      | Guaranteed by Process                          |
|               | 8.0  | Warp                                            | <40.00um                                      | Guaranteed by Process                          |
|               | 9.0  | Edge Exclusion                                  | 5 mm                                          | Guaranteed by Process                          |
| HandleSilicon | 10.0 | Handle Growth Method                            | CZ                                            | Wafer Vendor                                   |
|               | 11.0 | Handle Orientation                              | <111> off 2.5 - 3.5deg                        | Wafer Vendor                                   |
|               | 12.0 | Handle Thickness                                | 670.00 +/- 5.00 um                            | Guaranteed by Process                          |
|               | 13.0 | Handle Doping Type                              | P                                             | Wafer Vendor                                   |
|               | 14.0 | Handle Dopant                                   | Boron                                         | Wafer Vendor                                   |
|               | 15.0 | Handle Resistivity                              | < 0.005                                       | Wafer Vendor                                   |
|               | 16.0 | Backside Finish                                 | Lapped and etched with no oxide and lasermark | Wafer Vendor                                   |
| DeviceSilicon | 17.0 | Device Growth Method                            | FZ                                            | Wafer Vendor                                   |
|               | 18.0 | Device Orientation                              | <111> +/- 1 degree                            | Wafer Vendor                                   |
|               | 19.0 | Nominal Thickness                               | 381.00 +/- 2.00 um                            | ADE Single point, 100%                         |
|               | 20.0 | Distance to device silicon edge from wafer edge | <= 2mm                                        | Guaranteed by Process                          |
|               | 21.0 | Device Doping Type                              | P                                             | Guaranteed by Process                          |
|               | 22.0 | Device Dopant                                   | Boron                                         | Guaranteed by Process                          |
|               | 23.0 | Device Resistivity                              | 12000 - 20000 Ohmcm                           | Wafer Vendor                                   |
|               | 24.0 | Voids                                           | none                                          | Guaranteed by Process, SAM inspection          |
|               | 25.0 | Haze                                            | none                                          | Guaranteed by Process, Bright Light inspection |
|               | 26.0 | Scratches                                       | none                                          | Guaranteed by Process, Bright Light inspection |

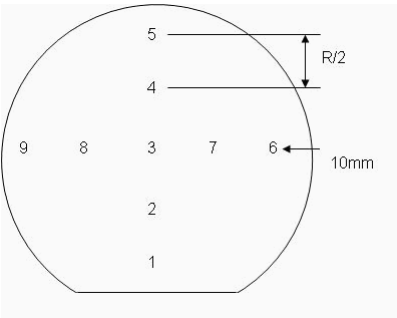
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|                   |                                                                                  |                                                                                         |                                                                                     |
|-------------------|----------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| Shipping Details  | Wafer per box :                                                                  | Max 25                                                                                  |  |
|                   | Packaging :                                                                      | Taped Polypropylene Wafer Box<br>Empak, Ultrapak, 100.00mm<br>Antistatic Double Bagging |                                                                                     |
|                   | Lot Shipment Data                                                                | Device Thickness<br>Bow / Warp Data<br>Handle and SOI Thickness                         |                                                                                     |
| Explanatory Notes | 1. Microscope inspection performed using microscope scan as below. 5x objective. |                                                                                         |                                                                                     |

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information